Abstracts

Review of SiGe process technology and its impact on RFIC design (2002 Vol. I [MWSYM])

A. Das, M. Huang, J. Mondal, D. Kaczman, C. Shurboff and S. Cosentino. "Review of SiGe process technology and its impact on RFIC design (2002 Vol. I [MWSYM])." 2002 MTT-S International Microwave Symposium Digest 02.1 (2002 Vol. I [MWSYM]): 171-174 vol.1.

In this paper, we review recently published SiGe BiCMOS technologies for RFIC design. Performance and integration trends in SiGe HBT's are discussed. The performance of passive devices, such as inductors, plays a key role in RF design. We review approaches to realizing high-Q inductor on a Si substrate. Finally, the interaction of HBT performance with design is illustrated through LNA design.

❑ Return to main document.